



**The Abdus Salam  
International Centre for Theoretical Physics**



**2015-1**

**Joint ICTP/IAEA Workshop on Advanced Simulation and Modelling  
for Ion Beam Analysis**

*23 - 27 February 2009*

**IBA XVI Complementary Techniques  
MEIS, LEIS, XRD, XRF, AES, TEM**

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# Complementary Techniques I

*Joint ICTP/IAEA Workshop on Advanced Simulation and Modelling for  
Ion Beam Analysis  
23 - 27 February 2009, Miramare - Trieste, Italy*

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**University of Surrey Ion Beam Centre**

**Guildford, England**

**Friday February 27<sup>th</sup> 2009**



IBA XVI: Complementary Techniques I

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- **Transmission Electron Microscopy**
- **Medium Energy Ion Scattering**
- **Low Energy Ion Scattering**
- **Auger Electron Spectroscopy**





## X-ray Fluorescence (XRF)



- X-rays in, X-rays out
  - Atomic de-excitation as for PIXE
- **COMPETITOR TECHNIQUE!**
- Fluorescence cross-sections  $\ll$  particle ionisation
  - XRF absolute sensitivity ~ nanograms
  - *cp.  $\mu$ PIXE absolute sensitivity ~ femtograms*
- XRF flavours
  - TRXRF: total reflection XRF
  - Sy-XRF: synchrotron XRF
  - Polarisation
  - Confocal techniques with polycapillary lenses
- Apparatus simple compared to PIXE
- Less beam damage with XRF





## XRF: when to use it? *use it when you can!*



- Incident X-ray beam more penetrating than protons
  - Advantage for XRF for thick homogeneous samples and coarse depth profiling of thick layered samples
  - Advantage for PIXE/EBS for thin layered samples
- XRF cross-section *decreases* towards lower energies
  - PIXE is opposite!
  - Sy-XRF can be used cleverly to distinguish close lines
- Quantification
  - Fundamental parameters: XRF (& PIXE) often hard
  - PIXE + backscattering is much easier
- Mapping clumsy for XRF
  - Real strength for  $\mu$ PIXE/EBS





# X-ray Diffraction (XRD)

*also applies to electron diffraction*



- **Interference method: essentially in reciprocal space**
  - no direct depth information
  - mathematically: Fourier transform of ensembles
  - selected area techniques give some 2D info
- **Unit cell dimensions**
  - Single crystals or polycrystalline samples
- **Texture**
  - preferred orientation
- **Grain Size**
  - Fourier transform of a constant is a delta function
  - limited grain size implies finite linewidth





# XRD Methods

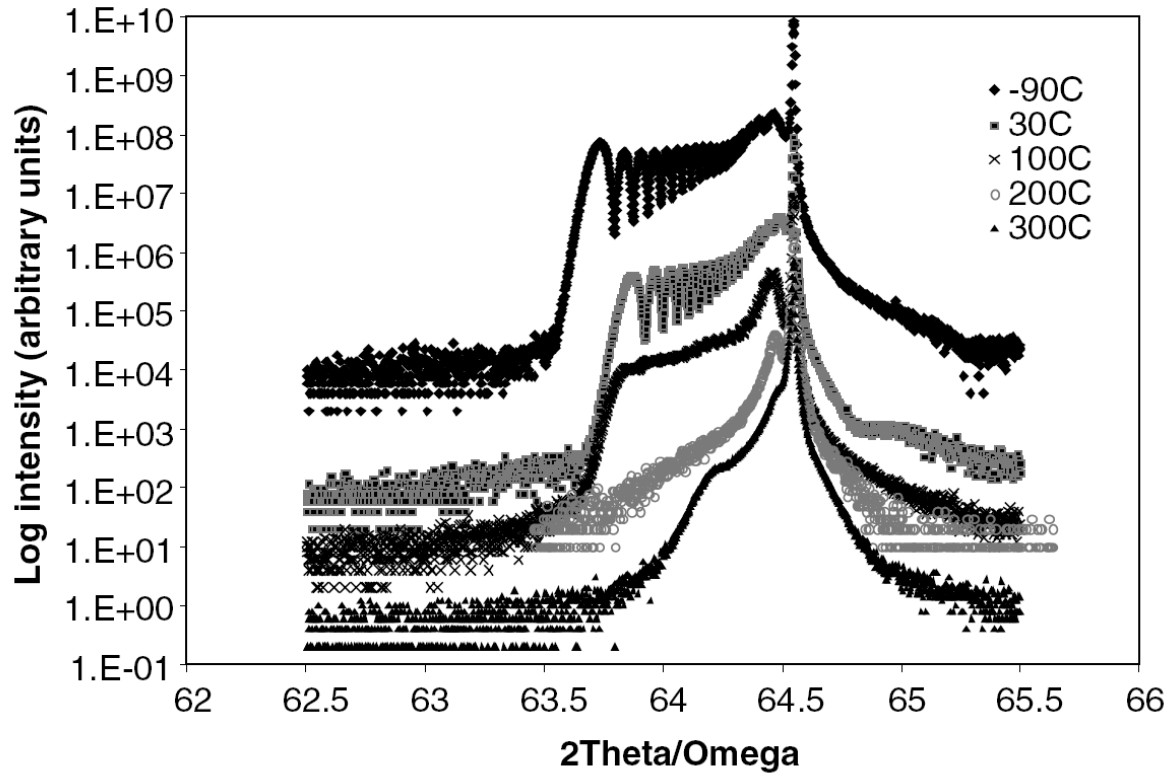


- Powder diffraction
- Single crystal
  - back-reflection or transmission Laue method (white)
  - rotating crystal (monochromatic)
  - Lang topography





# Single Crystal XRD



**Double axis X-ray diffraction (004)**

**GaAs with  $10^{17}$  H/cm<sup>2</sup>  
Different implantation temperatures shown**

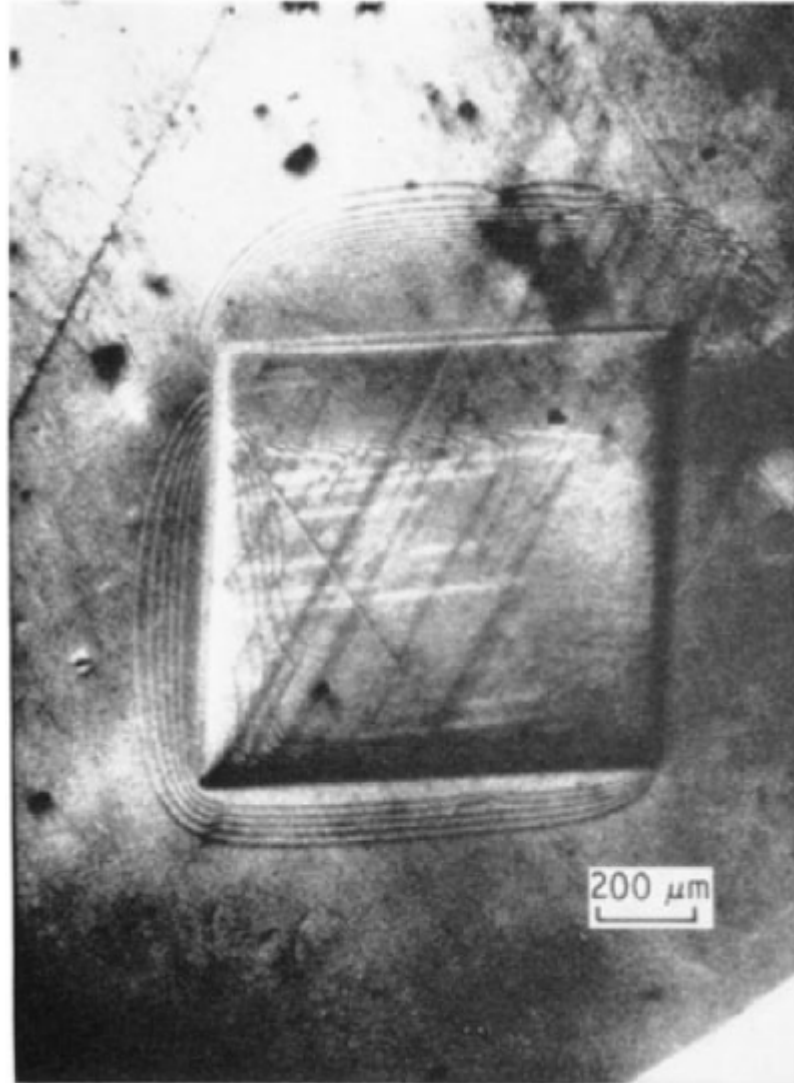
*The influence of the ion implantation temperature and the flux on smart-cut® in GaAs,*  
Webb M, Jeynes C, Gwilliam R, Too P, Kozanecki A, Domagala J, Royle A, Sealy B:  
*Nucl.Instrum.Methods B 240, 2005, 142-145*







# Lang Topography



## Lang Topograph

**Divergent beam stationary  
topograph of B-doped Si: Cu K $\beta$   
radiation**

*High resolution divergent beam X-  
ray topography, B.K.Tanner &  
C.J.Humphreys: J.Phys.D: 3,  
1970, 1144-1146 (2 plates)*

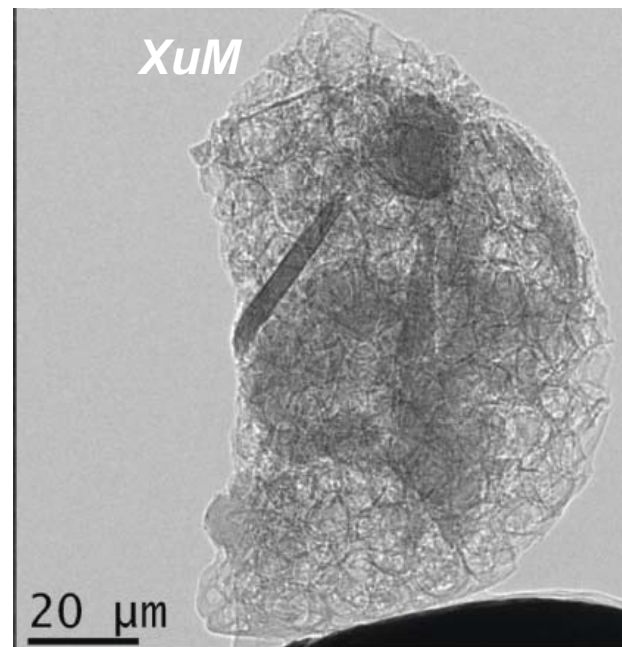
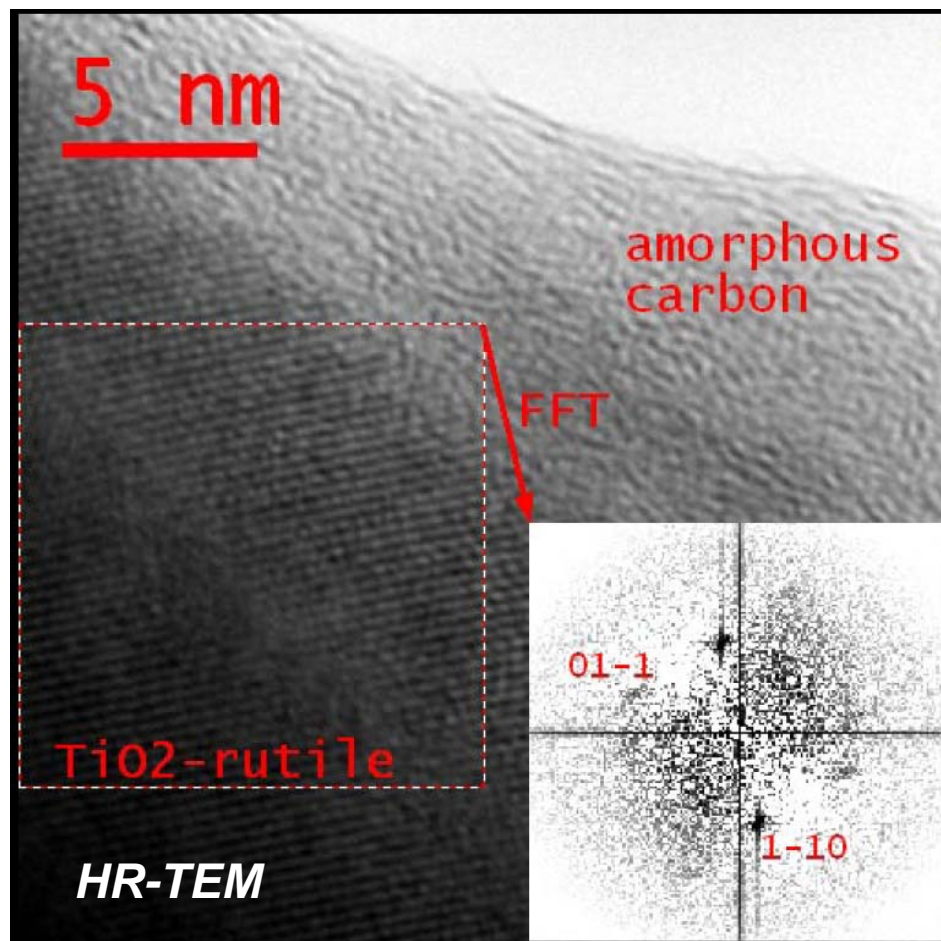
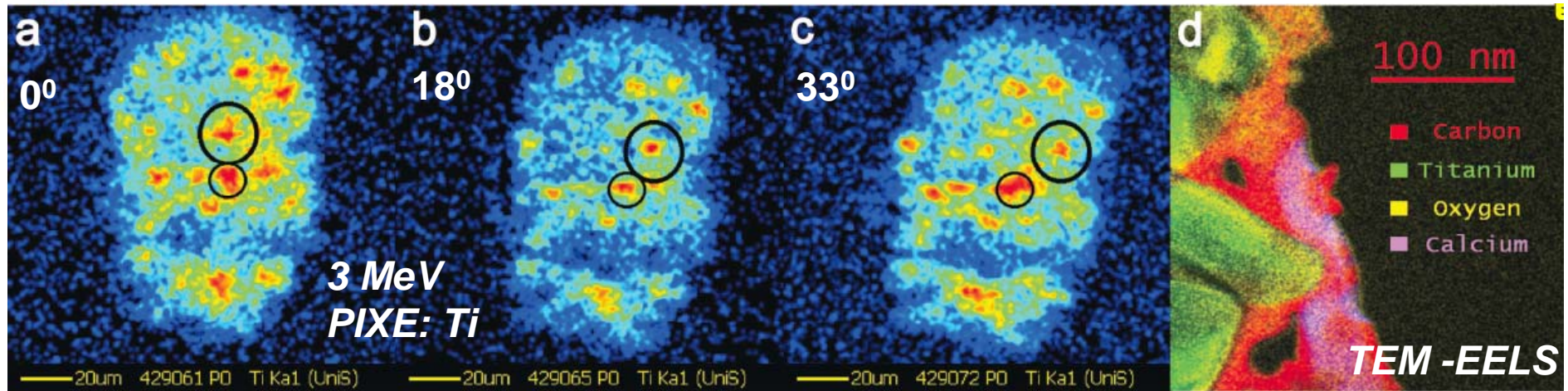


# Transmission Electron Microscopy (TEM)



- **Extraordinarily powerful set of techniques**
  - **imaging**
  - **high resolution (phase contrast)**
  - **ultra-high resolution (with aberration correction)**
  - **bright field / dark field (diffraction)**
  - **SAD (selected area diffraction)**
  - **EDX (quantitation hard)**
  - **EELS (electron energy loss spectroscopy): resonant absorption of electron energy at the atomic absorption edges give spatially resolved elemental information**
  - **confocal methods (STEM)**
  - **wonderful engineering**





**XuM: X-ray ultra-microscope**  
**X-ray tomography with ultra-focussing for high spatial resolution**

### **Inclusion in a Darwin impact glass: Ti micro-inclusions**

*The fate of organic carbon during meteorite impact: Kieren Howard, Melanie Bailey, Chris Jeynes, Vlad Stolojan et al, in preparation*



# Medium Energy Ion Scattering MEIS

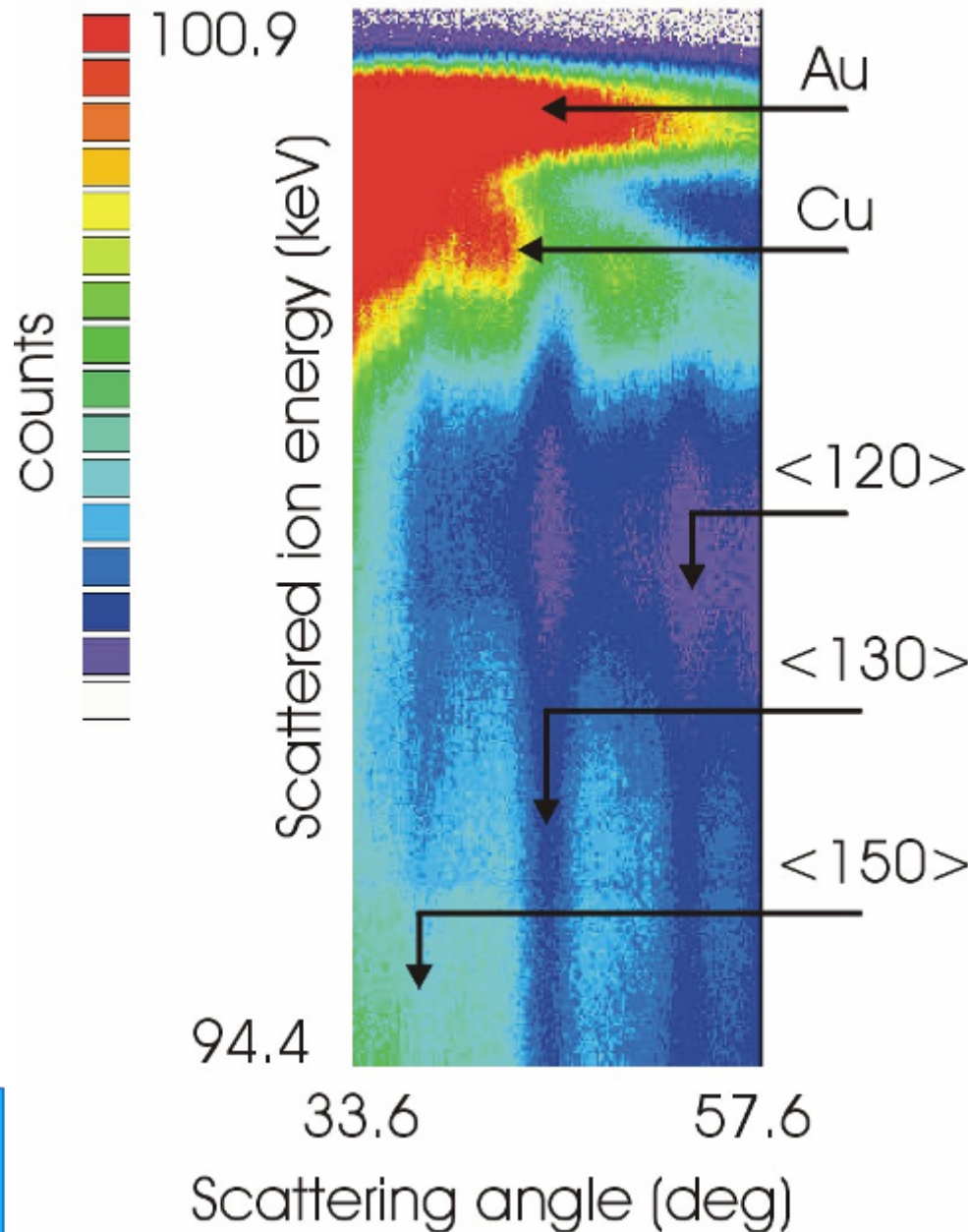


- **RBS, but with eg. 100 keV H<sup>+</sup> beam**
  - medium energy beam near maximum of stopping curve to maximise depth resolution
  - one atomic layer resolution in favourable cases
  - UHV required!
  - quantification hard: variable ionisation fraction
- **Sophisticated toroidal (electrostatic) detector**
  - energy and angle sensitive
  - simultaneous collection of all angles
- **Double alignment geometry**
  - surface structure determination





Cu(100)c(2x2)-Au



*Structure determination of the Cu(100)c(2x2)-Mn and Cu(100)c(2x2)-Au surface alloy phases by medium energy ion scattering, D.Brown, T.C.Q.Noakes, D.P.Woodruff, P.Bailey and Y.Le Goaziou, J.Phys.: Condens.Matter 11 (1999) 1889-1901*



# Low Energy Ion Scattering LEIS



- **RBS, but with eg. 5 keV He<sup>+</sup>**
  - Highly sensitive to *first atomic layer*
  - Electrostatic toroidal detector similar to MEIS
  - Shadow cones too large for high angular sensitivity
  - Depth profiling (to 10nm!) with ion sputtering
- **Applications**
  - Extraordinarily valuable where the surface configuration is critical
  - Catalysts
  - Adhesion
  - Wetting

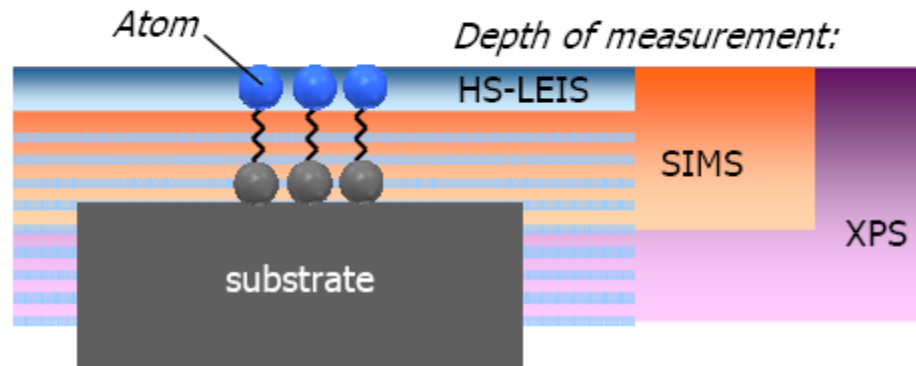




# High Sensitivity LEIS

“Calipso” company (Hidde Brongersma)

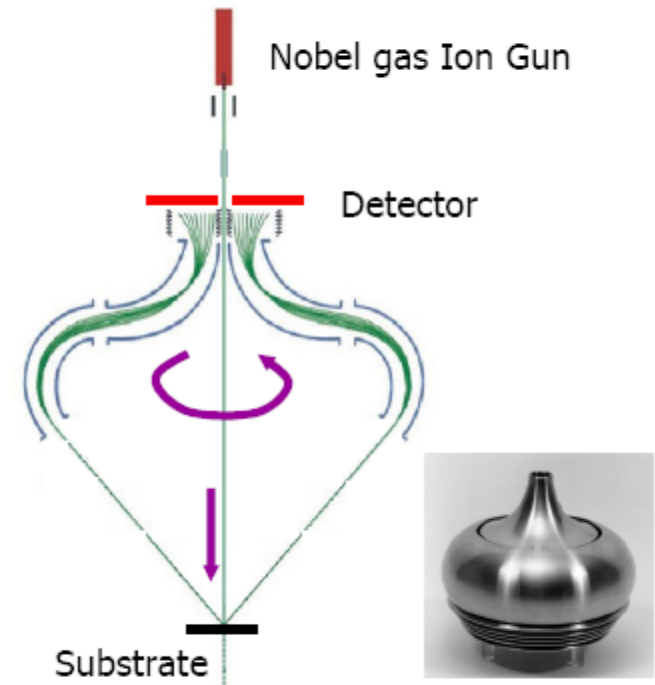
## HS-LEIS compared to SIMS and XPS:



*schematic representation of cross section of surface*

- HS-LEIS** - quantitative 1st atomic layer  
- in-depth profile 0-10 nm (shaded area)
- SIMS** - not quantitative (for 1<sup>st</sup> atomic layer)  
- chemical information
- XPS** - information depth of 3 – 10 nm

## Unique HS-LEIS analyzer:



Picture of analyzer





# Auger Electron Spectroscopy

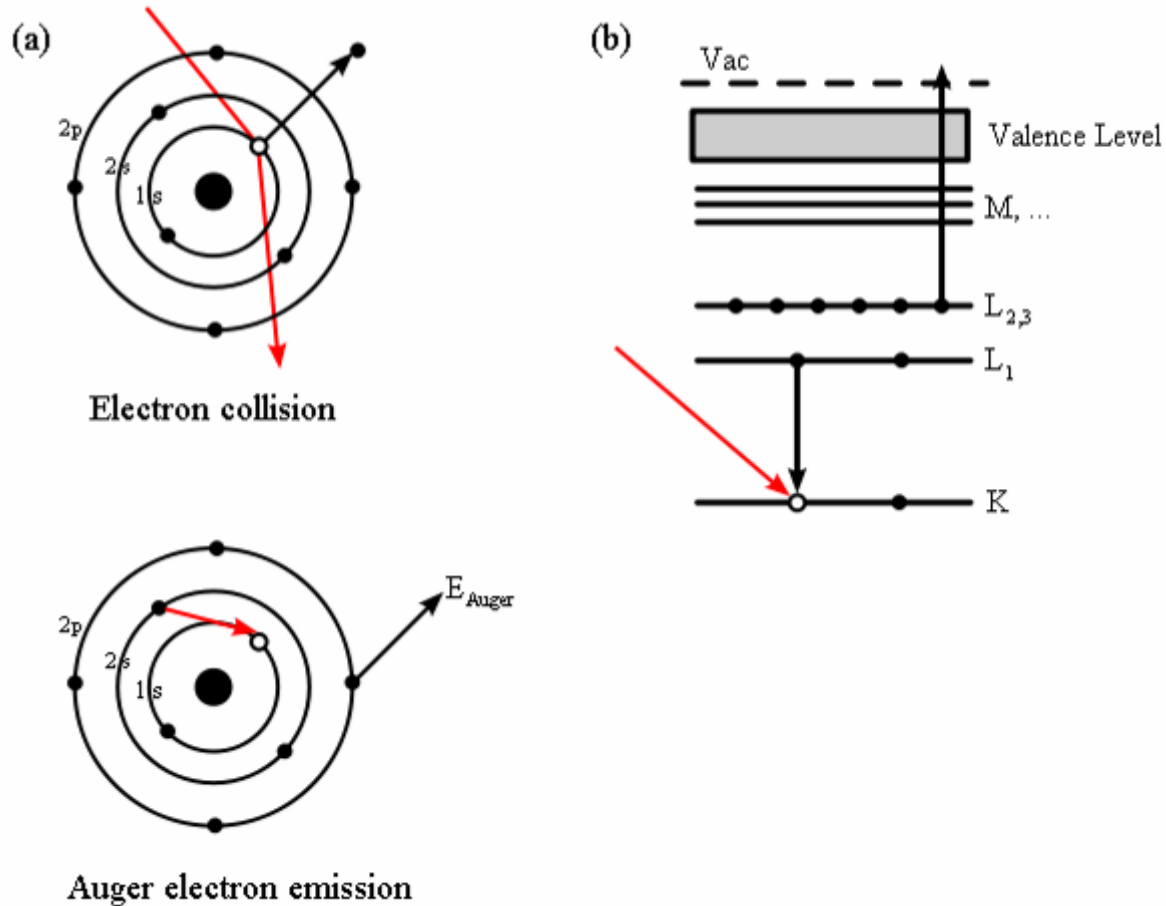


- **Surface Science technique (UHV)**
- **Electrons ionise target, Auger electrons detected**
  - scanning electron microscope (SEM) technique
  - information depth from the *inelastic mean free path* hence a surface method
- **Auger electron energy spectrum: characteristic lines**
  - good elemental sensitivity
  - chemical information (valence electrons) present only obscurely in Auger process. The primary photoelectron process (XPS) is clearer
  - spacial resolution almost that of the electron beam





# Auger Mechanism



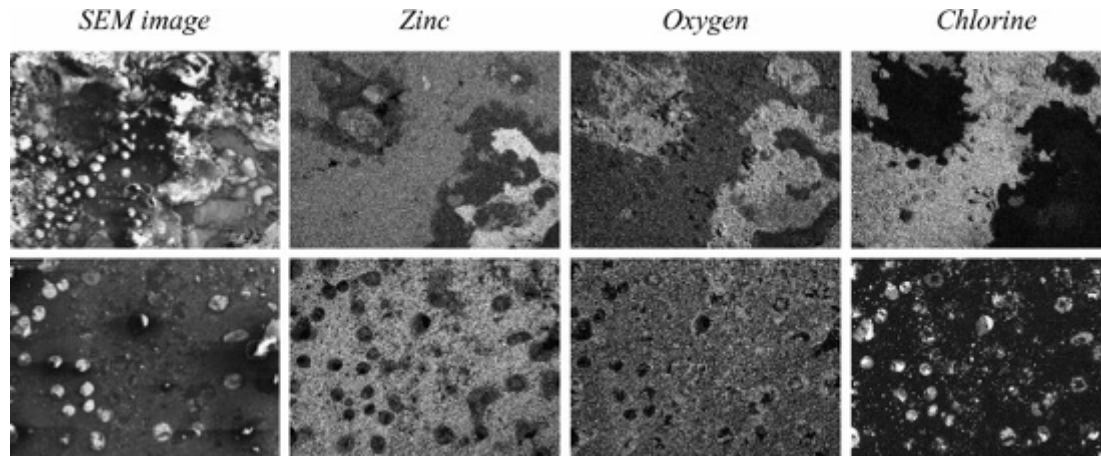


Fig. 9. SEM image and elemental composition analyzed by EDX for Zn (top) and ZnMg<sub>2</sub> (bottom) exposed with NaCl deposits (magnification ×30).

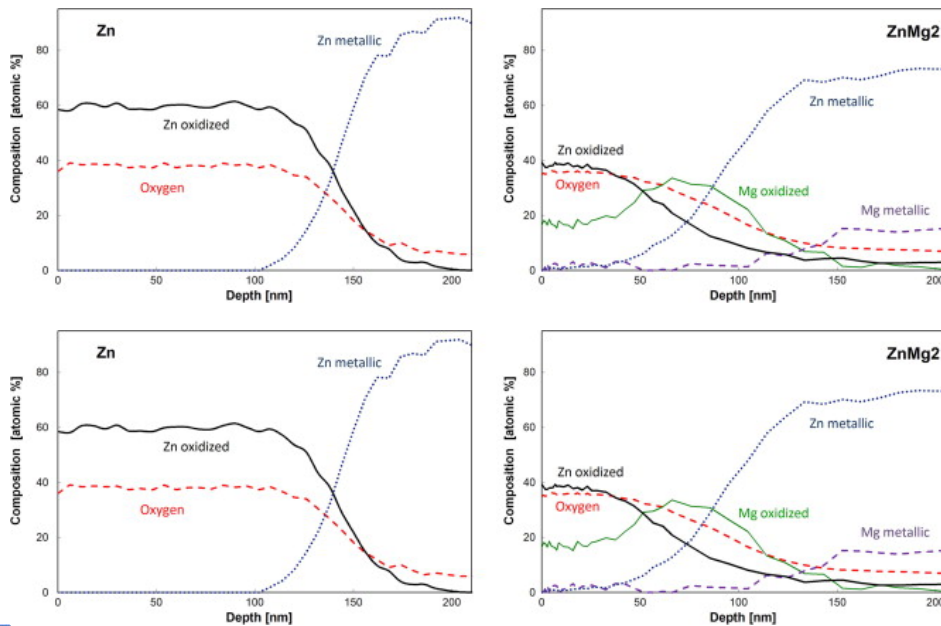


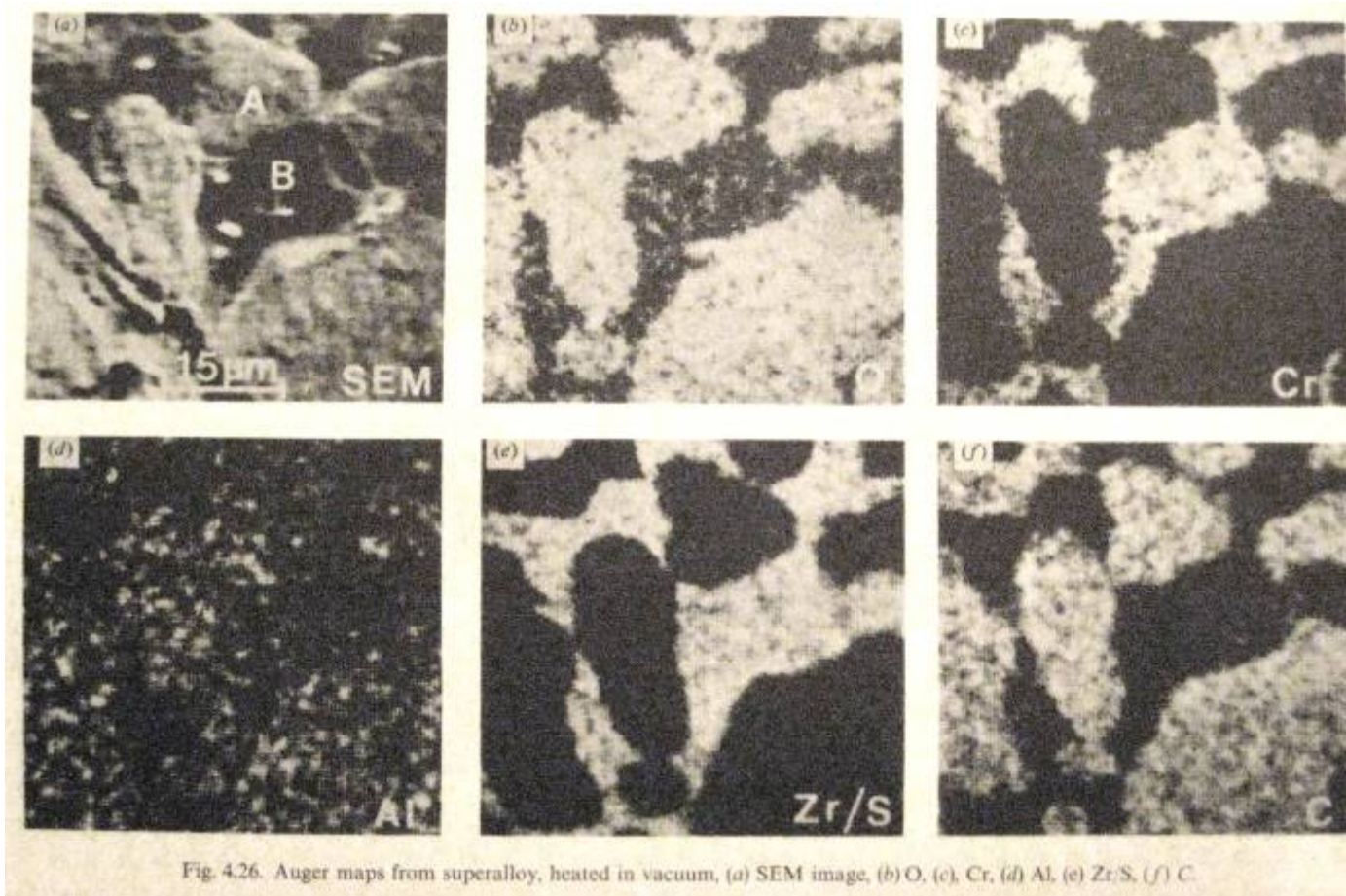
Fig. 10. AES depth profiles of untreated Zn and ZnMg<sub>2</sub> exposed for 28 days at 20 °C and 80% RH.

Fig. 11. AES depth profiles of Zn and ZnMg<sub>2</sub> with deposited 1.40 g/m<sup>2</sup> chloride and exposed for 28 days at 20 °C and 80% RH.



**Corrosion mechanism of model zinc–magnesium alloys in atmospheric conditions, T. Prosek, A. Nazarov, U. Bexell, D. Thierry and J. Serak, Corrosion Science 50, 2008, 2216-2231**

# Scanning Auger Microscopy



Phase segregation of superalloy, ion cleaned and heated to 350°C. The A phase is rich in Cr & Zr, the B phase has high C & O



# General Remarks

Not many critical comparative studies  
Here is a recent example



SURFACE AND INTERFACE ANALYSIS  
*Surf. Interface Anal.* 2004; **36**: 1269–1303  
Published online 1 September 2004 in Wiley InterScience (www.interscience.wiley.com). DOI: 10.1002/sia.1909

## Critical review of the current status of thickness measurements for ultrathin SiO<sub>2</sub> on Si Part V: Results of a CCQM pilot study

M. P. Seah,<sup>1\*</sup> S. J. Spencer,<sup>1</sup> F. Bensebaa,<sup>2</sup> I. Vickridge,<sup>3</sup> H. Danzebrink,<sup>4</sup> M. Krumrey,<sup>5</sup> T. Gross,<sup>6</sup> W. Oesterle,<sup>7</sup> E. Wendler,<sup>8</sup> B. Rheinländer,<sup>9</sup> Y. Azuma,<sup>10</sup> I. Kojima,<sup>10</sup> N. Suzuki,<sup>11</sup> M. Suzuki,<sup>12</sup> S. Tanuma,<sup>13</sup> D. W. Moon,<sup>14</sup> H. J. Lee,<sup>15</sup> Hyun Mo Cho,<sup>16</sup> H. Y. Chen,<sup>17</sup> A. T. S. Wee,<sup>18</sup> T. Osipowicz,<sup>19</sup> J. S. Pan,<sup>20</sup> W. A. Jordaan,<sup>21</sup> R. Hauert,<sup>22</sup> U. Klotz,<sup>22</sup> C. van der Marel,<sup>23</sup> M. Verheijen,<sup>23</sup> Y. Tamminga,<sup>24</sup> C. Jeynes,<sup>25</sup> P. Bailey,<sup>26</sup> S. Biswas,<sup>27</sup> U. Falke,<sup>28</sup> N. V. Nguyen,<sup>29</sup> D. Chandler-Horowitz,<sup>29</sup> J. R. Ehrstein,<sup>29</sup> D. Muller<sup>30</sup> and J. A. Dura<sup>31</sup>

(see Appendix for addresses)

Received 7 January 2004; Revised 29 March 2004; Accepted 29 March 2004

**SIA**

**Complementary Techniques: XPS, SIMS, TEM, ellipsometry, GIXRR (grazing incidence Sy-X-ray reflectometry at BESSY), neutron reflectometry (NIST), MEIS, NRA, EBS, RBS**

**HR-TEM and MEIS much more equivocal than expected**

**NRA anomalous (7%)**

**Neutron reflectometry very low uncertainties (<1%): absolute interference method**

**RBS/EBS absolute uncertainty 6%**

**With new value of IMFP determined by this work, XPS achieved uncertainties of 2% (k=1)**



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## Summary



- **PIXE, XRF, AES (and XPS), EELS are all variants of the same atomic excitation process**
- **The same diffraction techniques are seen with X-rays and electrons**
- **The same scattering process is seen in RBS (etc), MEIS, LEIS**
- **Similar types of mapping capabilities are seen with  $\mu$ beam IBA, AES (SAM), TEM**
- **Some *textbook* examples can be *better* done with IBA**
- **IBA *inferior* in other cases**
- **Many cases where IBA and other methods strictly *complementary***

